	Application No.	Applicant(s)	ØK
	10/619,981	BAUKUS ET AL.	er e
Notice of Allowability	Examiner	Art Unit	
	Walter L. Lindsay, Jr.	2812	
Th MAILING DATE of this communication appe All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in this ap or other appropriate communication GHTS. This application is subject t	pplication. If not included n will be mailed in due c	d ourse. THIS
1. This communication is responsive to <u>divisional</u> .			
2. The allowed claim(s) is/are 5-8,13 and 14.			
3. The drawings filed on 15 July 2003 are accepted by the Examiner.			
 4. Acknowledgment is made of a claim for foreign priority una a) All b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). * Certified copies not received: 	been received. been received in Application No		on from the
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		complying with the requ	uirements
5. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give			OTICE OF
 6. CORRECTED DRAWINGS (as "replacement sheets") muss (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the deposant sheet of the deposant sheet o	on's Patent Drawing Review (PTO s Amendment / Comment or in the (84(c)) should be written on the drawine header according to 37 CFR 1.121 sit of BIOLOGICAL MATERIAL	Office action of ngs in the front (not the I (d). must be submitted. N	
 Attachm nt(s) 1. ☑ Notice of References Cited (PTO-892) 2. ☐ Notice of Draftperson's Patent Drawing Review (PTO-948) 3. ☑ Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date 5/17/2004 4. ☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material 	5. Notice of Informal F 6. Interview Summary Paper No./Mail Da 7. Examiner's Amend 8. Examiner's Statem 9. Other	(PTO-413), ate ment/Comment	

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DETAILED ACTION

Allowable Subject Matter

1. Claims 5-8 and 13-14 are allowed.

The following is an examiner's statement of reasons for allowance: the prior art, 2.

either singly or in combination fails to anticipate or render obvious, the limitations of:

... forming first and second buried silicon regions of a second conductivity type

within the silicon substrate of the first conductivity type;

depositing a first polycrystaliline silicon layer, said first polycrystalline silicon layer

contacting said first buried silicon regions;

depositing a second insulating layer over the first insulating layer, the first

polycrystalline silicon layer and the second buried silicon regions; and

depositing a second polycrystalline silicon layer over said second insulating layer

and said second buried silicon regions of the second conductivity type, said second

buried silicon regions of the second conductivity type, said second buried silicon regions

of the second conductivity type being insulated from said second polycrystalline silicon

layer, as required by claim 1.

The prior art, either singly or in combination fails to anticipate or render obvious, the

limitations of:

... forming buried silicon regions of a second conductivity type within the silicon

substrate of the first conductivity type;

depositing a first polycrystalline silicon layer over the silicon substrate of the first

conductivity type; and

depositing a second polycrystalline silicon layer over the silicon substrate of the first conductivity type,

wherein a first portion of said buried silicon regions of the second conductivity type contacts the first polycrystalline silicon layer and is isolated from the second polycrystalline silicon layer, and a second portion of said buried silicon regions is insulated from the first and the second polycrystalline silicon layer, as required by claim 13.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Walter L. Lindsay, Jr. whose telephone number is (571) 272-1674. The examiner can normally be reached on Monday-Thursday.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John F Niebling can be reached on (571) 272-1679. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

WLL Walles Linels M July 6, 2004

> /John F. Niebling Supervisory Patent Examiner Technology Center 2800